**Product data sheet** 

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic-level compatible
- Very fast switching
- · Trench MOSFET technology
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	60	V		
$V_{GS}$	gate-source voltage			-20	-	20	V		
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	320	mA		
Static characte	Static characteristics								
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}; T_j = 25 \text{ °C}$		-	1	1.6	Ω		

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



60 V, dual N-channel Trench MOSFET

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		D <sub>1</sub> D <sub>2</sub>
2	G1	gate 1	6 5 4	
3	D2	drain 2		
4	S2	source 2		
5	G2	gate 2	∐1 ∐2 ∐3	$\begin{bmatrix} & & & & & & \\ & & & & & & \\ & & & & & $
6	D1	drain 1	TSSOP6 (SOT363)	31 G1 G2 G2 msd901

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
2N7002HS		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
2N7002HS	C7%

[1] % = placeholder for manufacturing site code

### 60 V, dual N-channel Trench MOSFET

## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or					
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	320	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	200	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T <sub>sp</sub> = 25 °C		-	960	mW
Per device			'			
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	420	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode		'	1		
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	320	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

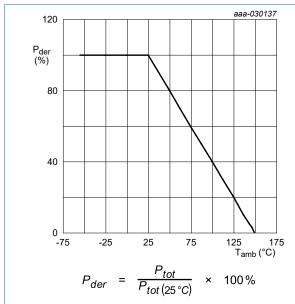


Fig. 1. Normalized total power dissipation as a function of ambient temperature

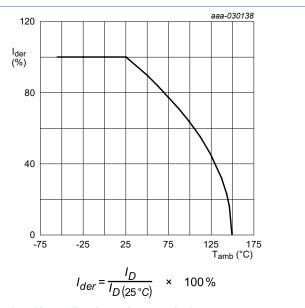


Fig. 2. Normalized continuous drain current as a function of ambient temperature

## 60 V, dual N-channel Trench MOSFET

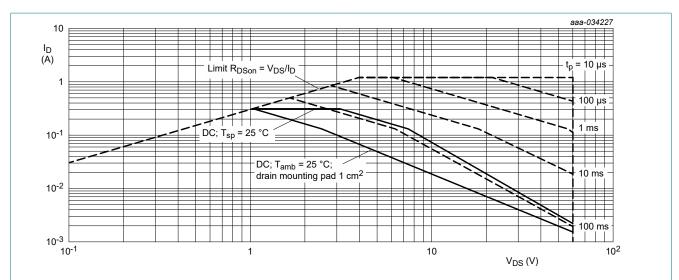


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

60 V, dual N-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device	'		,				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W
Per transist	tor			'		'	
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	390	445	K/W
	junction to ambient		[2]	-	340	390	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

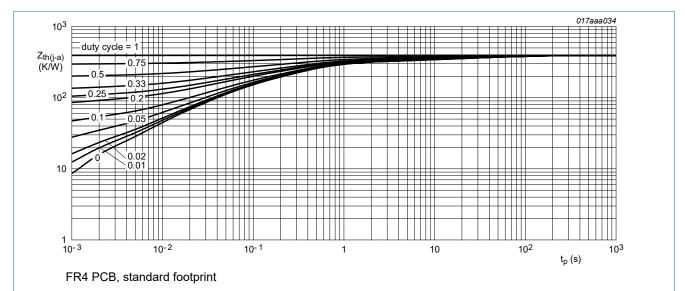


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

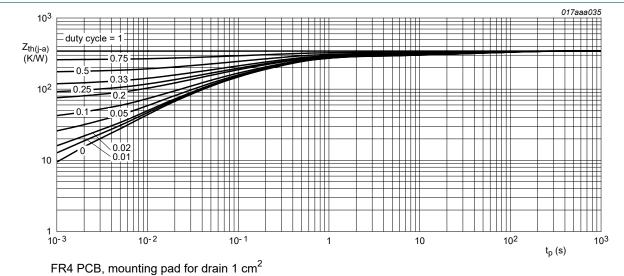


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

2N7002HS

## 60 V, dual N-channel Trench MOSFET

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.75	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C	-	1	1.6	Ω
resistance		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 150 °C	-	2.1	3.3	Ω
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 50 mA; T <sub>j</sub> = 25 °C	-	1.3	2	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	400	-	mS
Dynamic ch	aracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 300 mA; V <sub>GS</sub> = 4.5 V;	-	0.3	0.5	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	34	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	3	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	6	-	ns
t <sub>f</sub>	fall time		-	4	-	ns
Source-drai	in diode		'			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	0.47	0.75	1.1	V

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### 60 V, dual N-channel Trench MOSFET

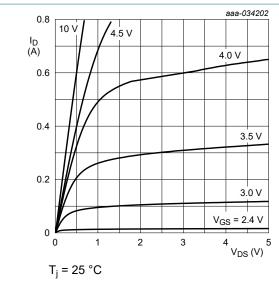


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

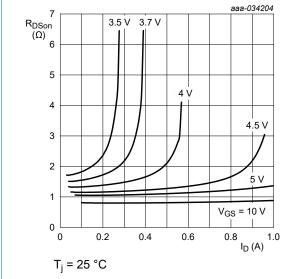


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

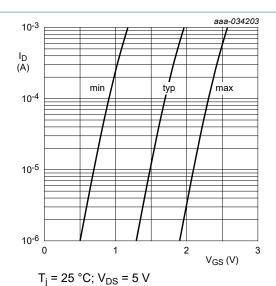


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

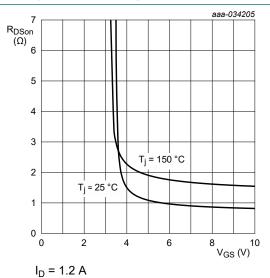


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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### 60 V, dual N-channel Trench MOSFET

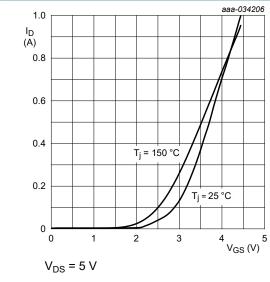


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

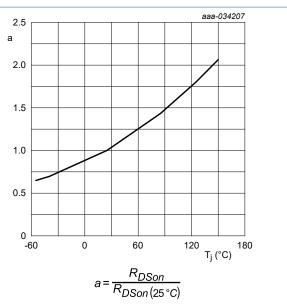


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

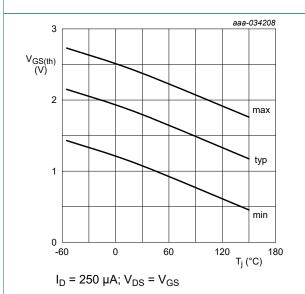


Fig. 12. Gate-source threshold voltage as a function of junction temperature

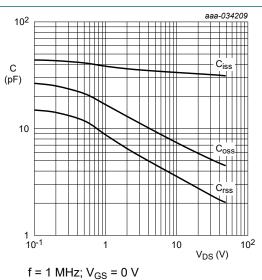


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

## 60 V, dual N-channel Trench MOSFET

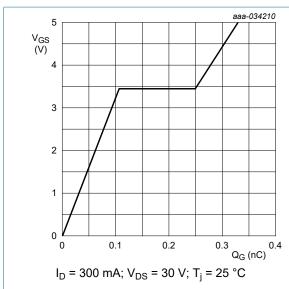


Fig. 14. Gate-source voltage as a function of gate charge; typical values

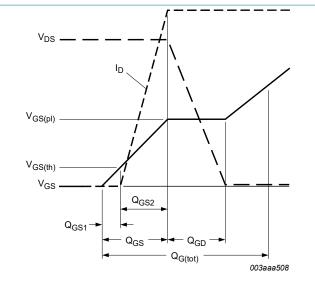


Fig. 15. Gate charge waveform definitions

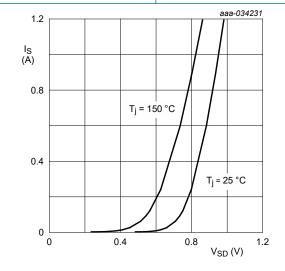
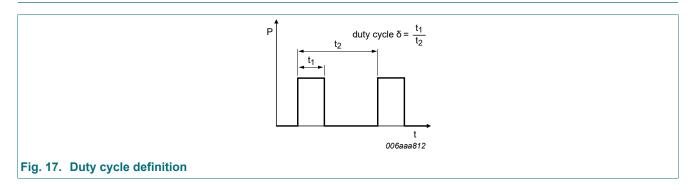


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

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## 11. Test information



## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 60 V, dual N-channel Trench MOSFET

# 12. Package outline

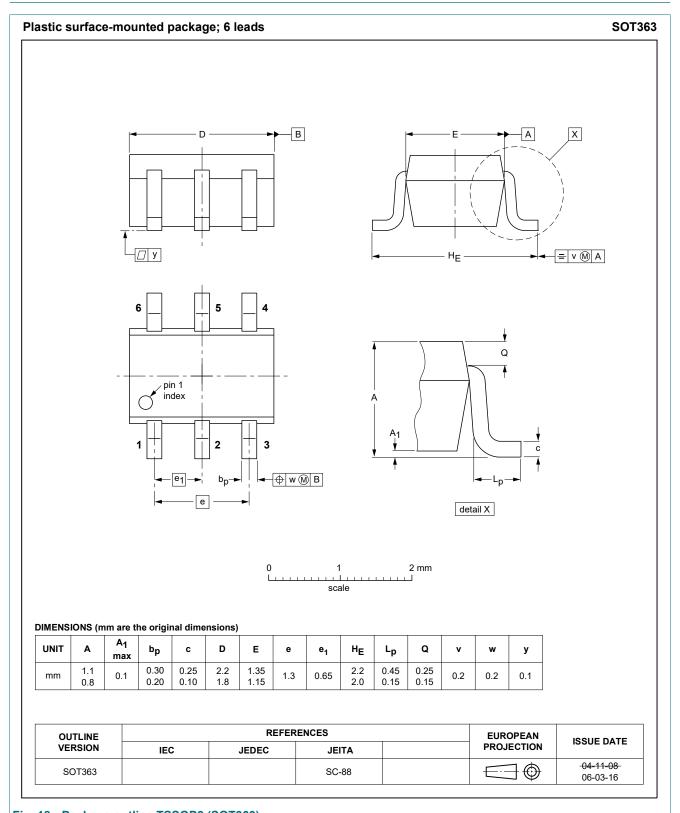
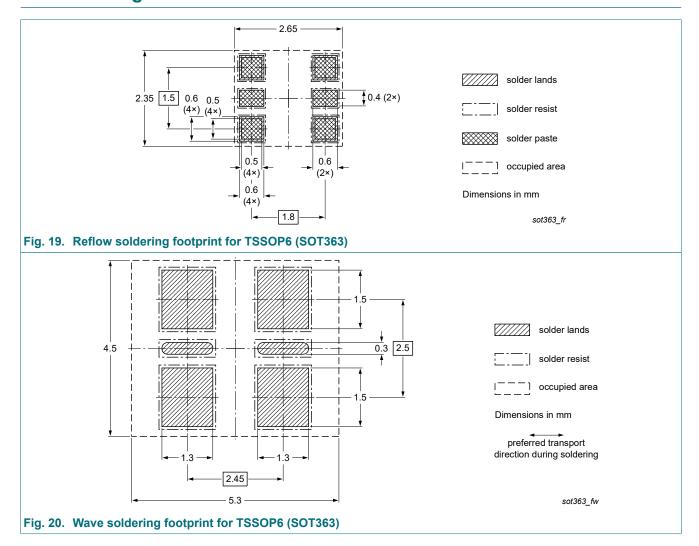


Fig. 18. Package outline TSSOP6 (SOT363)

### 60 V, dual N-channel Trench MOSFET

# 13. Soldering



## 60 V, dual N-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
2N7002HS v.3	20211215	Product data sheet	-	2N7002HS v.2			
Modifications:	Changed values for	Changed values for parameters I <sub>D</sub> and I <sub>S</sub>					
2N7002HS v.2	20211201	Product data sheet	-	2N7002HS v.1			
2N7002HS v.1	20211119	Preliminary data sheet	-	-			

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#### 60 V, dual N-channel Trench MOSFET

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## 60 V, dual N-channel Trench MOSFET

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